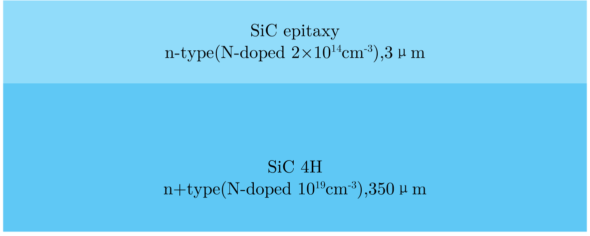
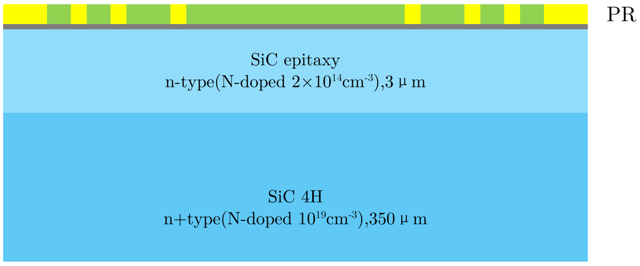
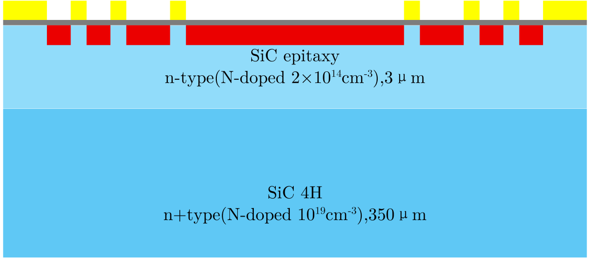
1. 画出保护环终端的器件流程图



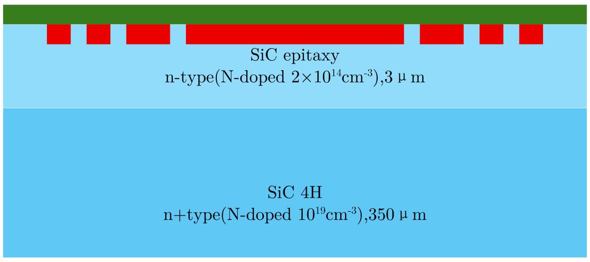
1.硅晶圆



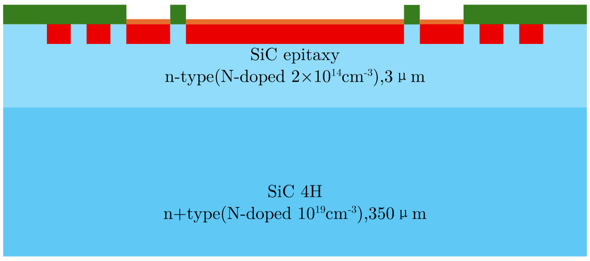
2.沉积SiO^2，旋涂光刻胶



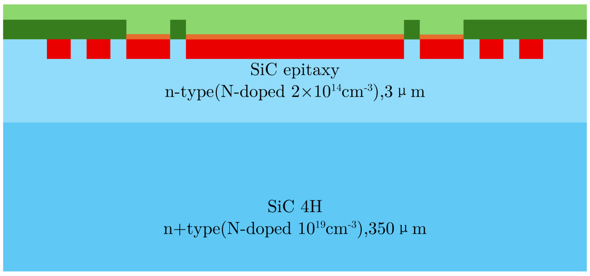
3.光刻并离子注入Al



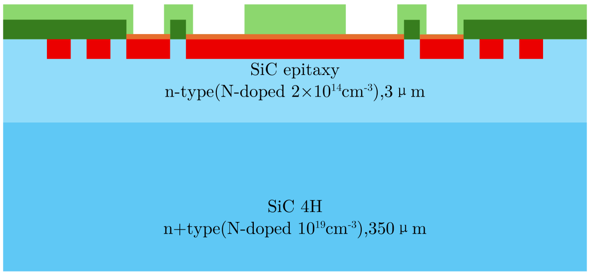
4.洗去SiO$_2$和光刻胶，沉积隔离介质SiO$_2$



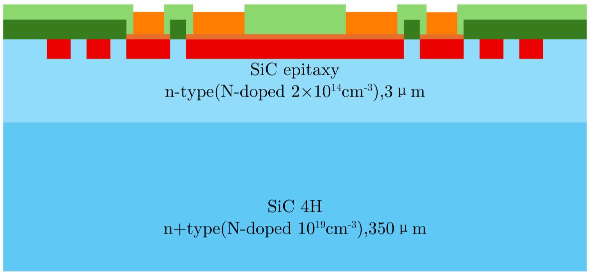
5.刻蚀SiO$_2$，磁控溅射欧姆接触金属电极Ti/Al/Ti/Ni



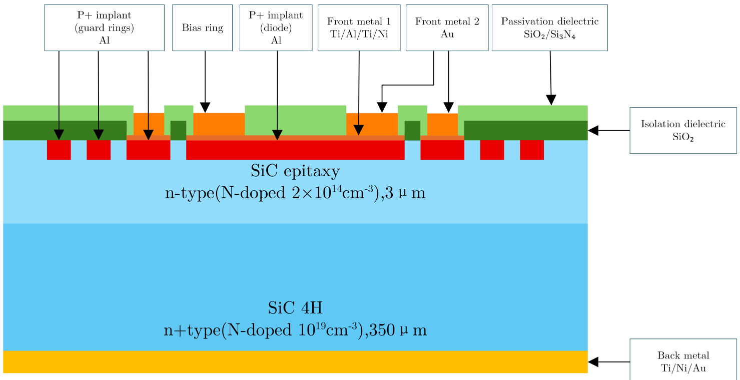
6.钝化介质层SiO$_2$/Si$_3$N$_4$



7.刻蚀介质层



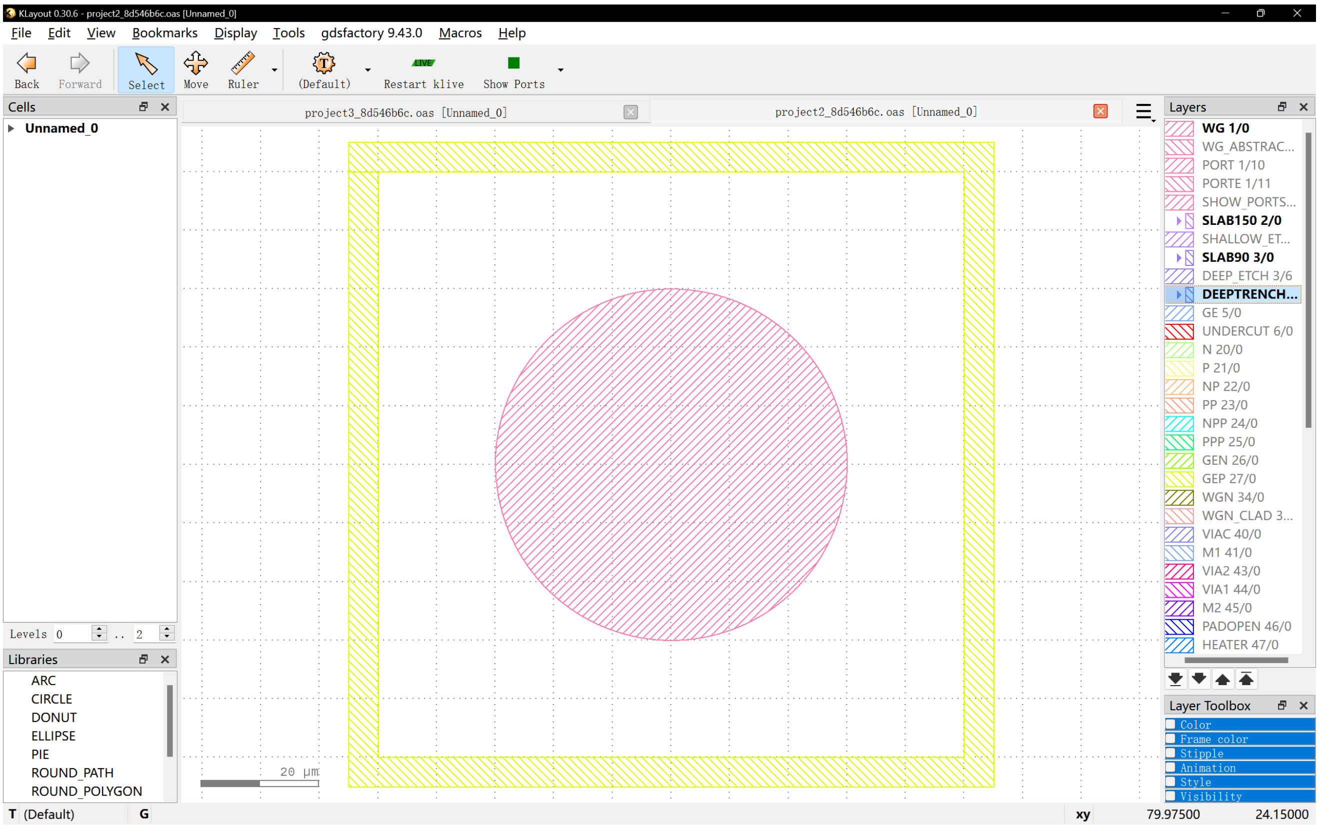
8.磁控溅射欧姆接触金属电极Au



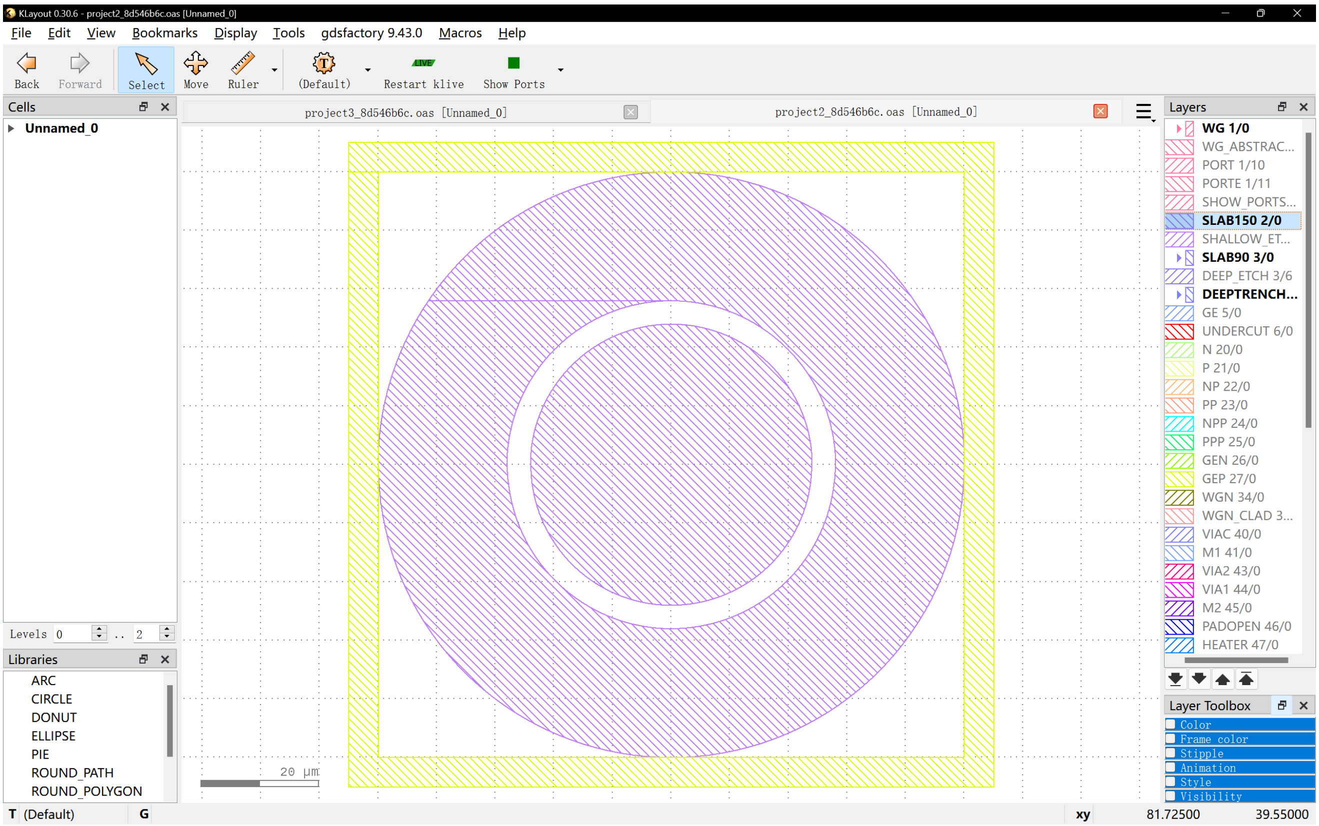
9.衬底减薄+背部金属沉积

2.画出刻蚀终端器件的光刻板

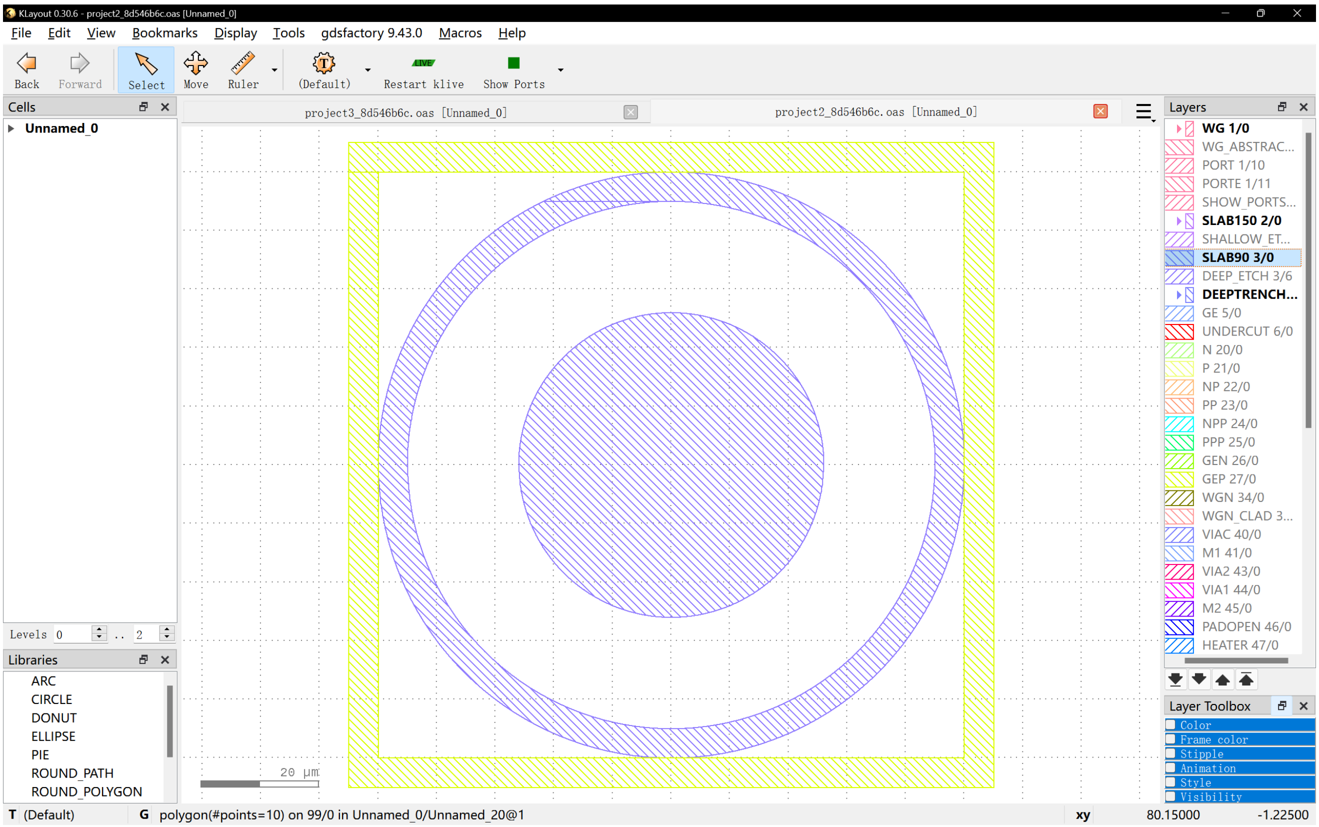
(1)圆形器件



> *第一层：［②刻蚀终端过刻至增益层以下］的光刻板*

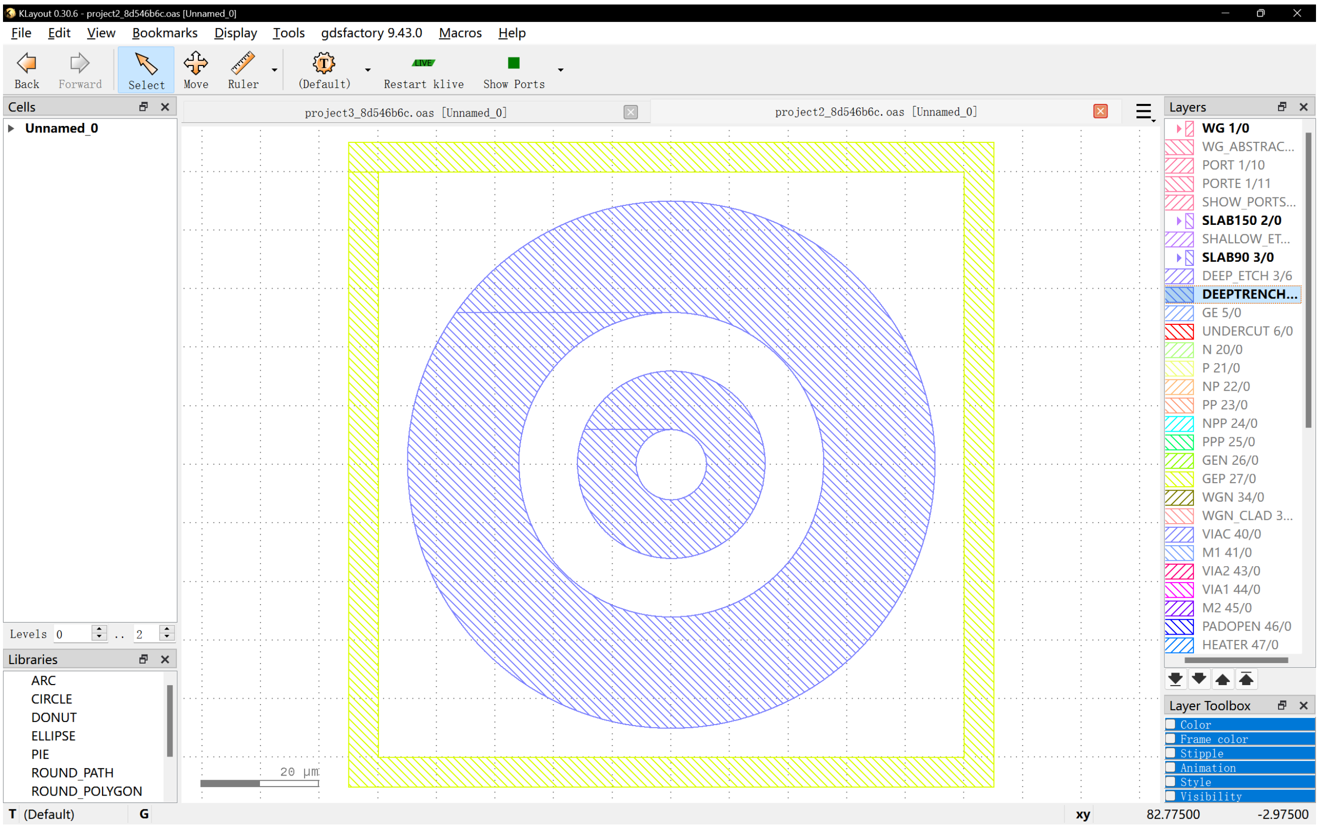


第二层：【④刻蚀钝化层】的光刻板



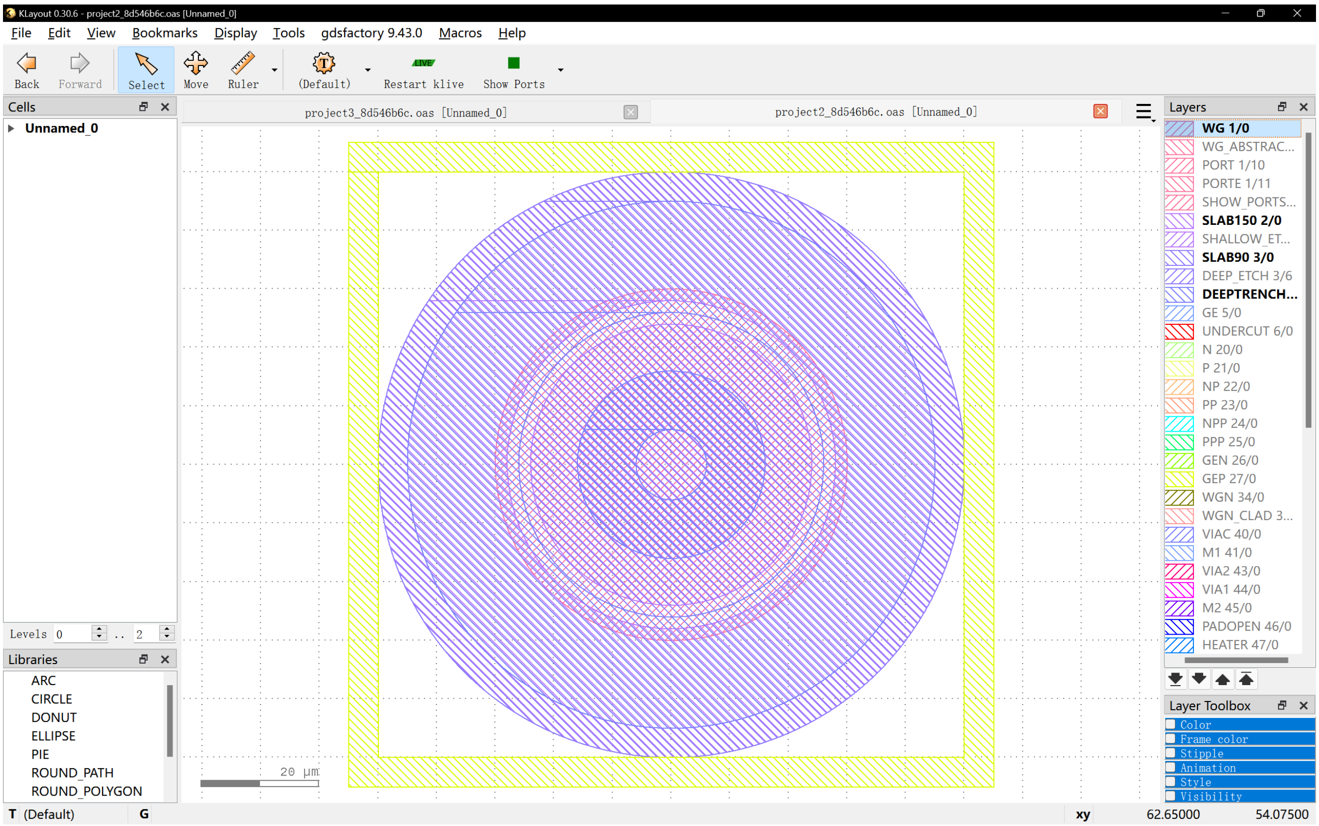
T (Default) G polygon(#points=10) on 99/0 in Unnamed_0/Unnamed_20@1 xy 80.15000 -1.22500

第三层：【⑦刻蚀钝化层】的光刻板



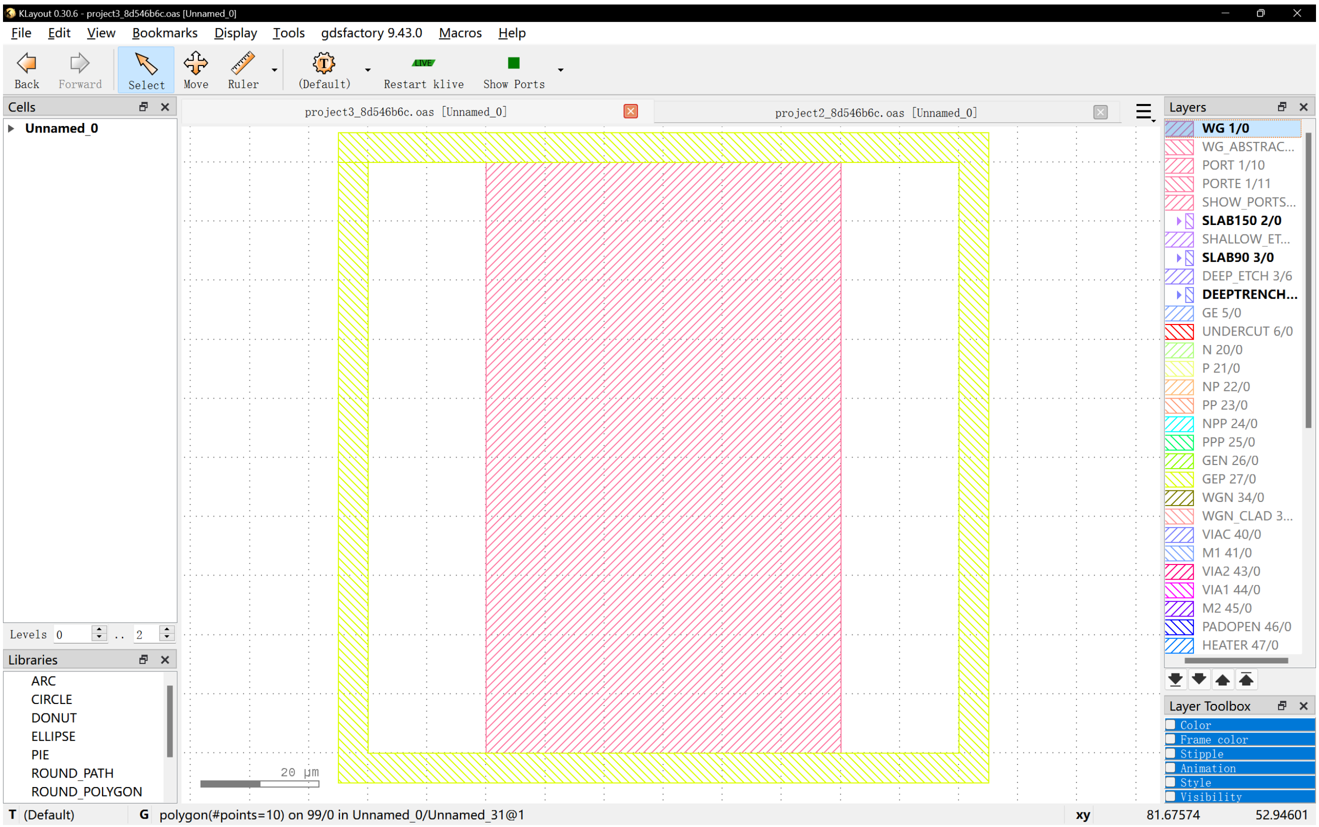
T (Default) G xy 82.77500 -2.97500

第四层：【⑧沉积PAD金属+场板】的光刻板



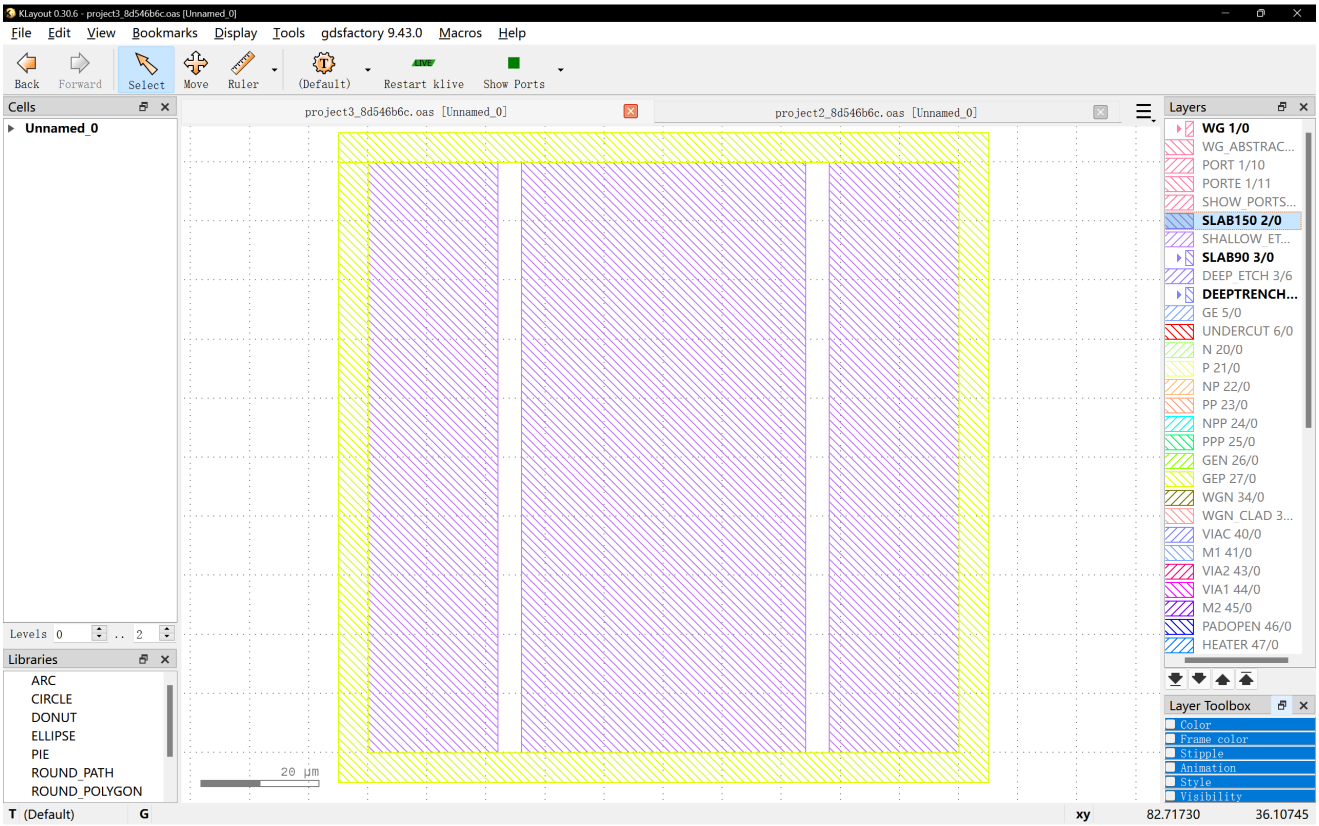
> 光刻板总览

(2)方形器件

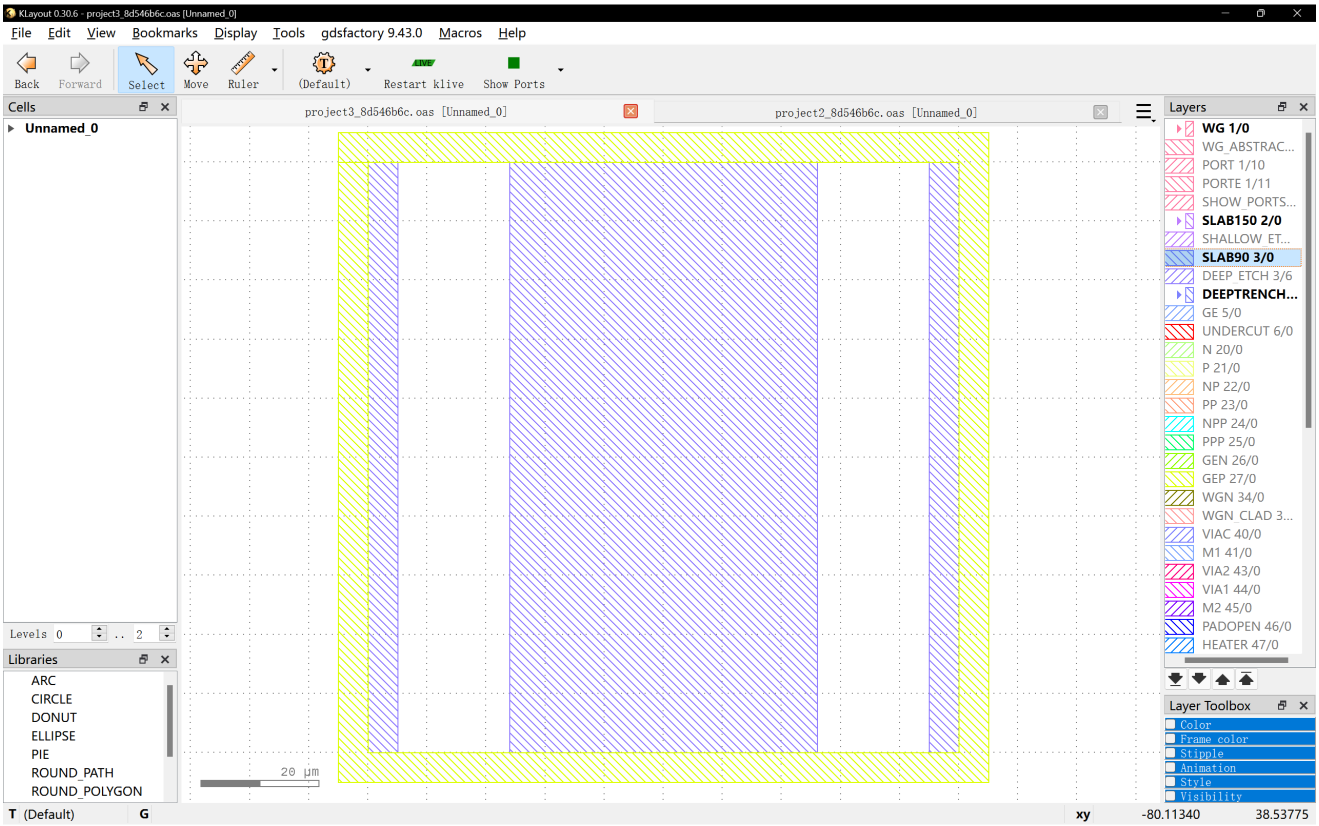


polygon(#points=10) on 99/0 in Unnamed_0/Unnamed_31@1

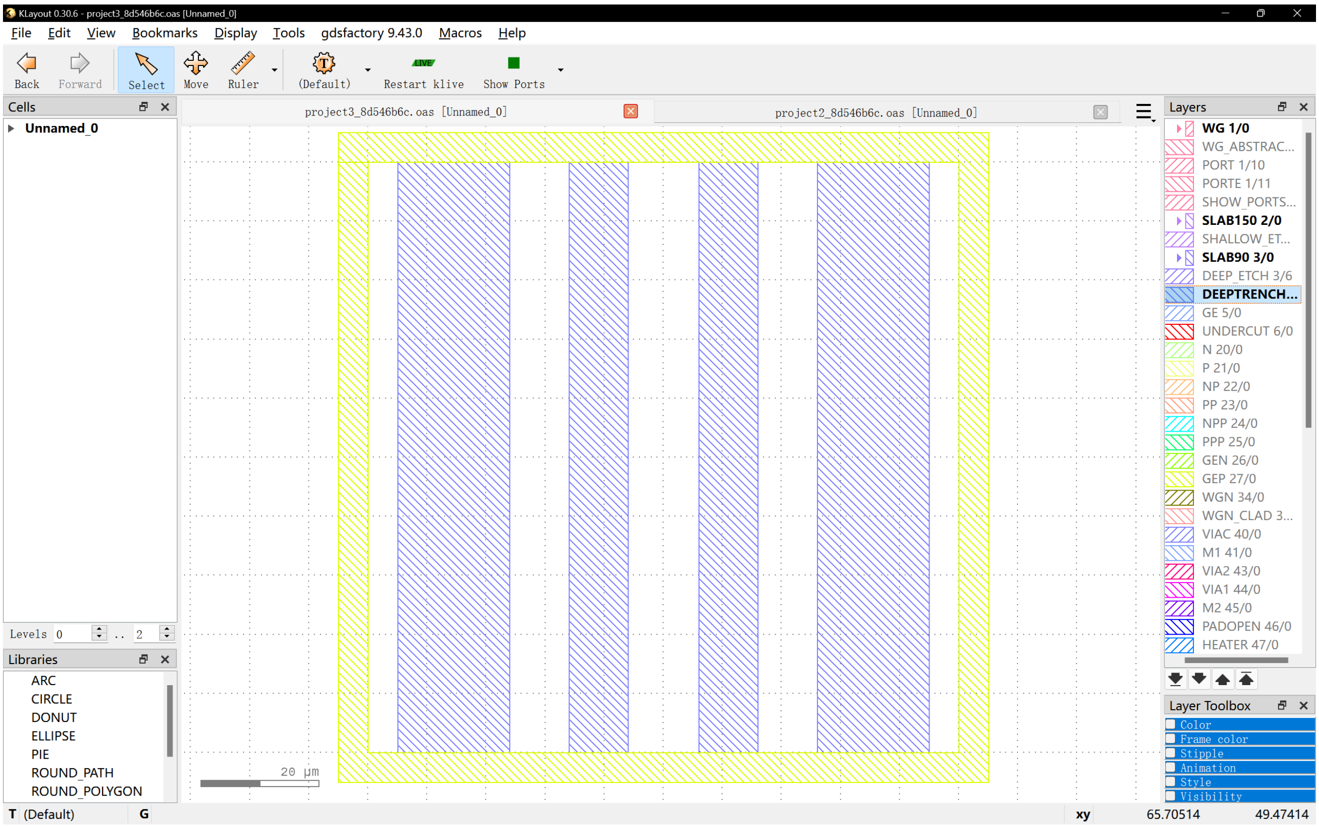
> 第一层：[②刻蚀终端过刻至增益层以下]的光刻板



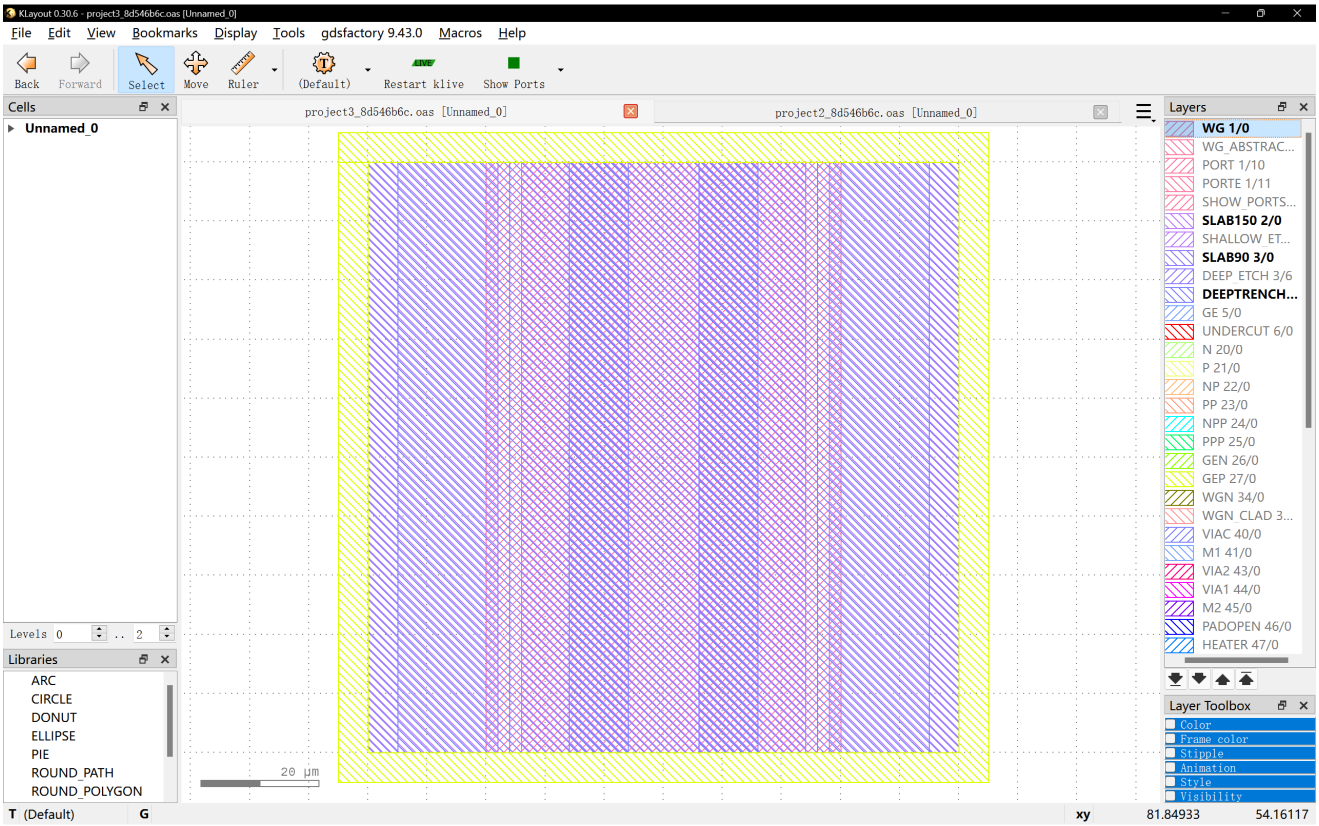
> 第二层：［④刻蚀钝化层］的光刻板



> 第三层：［⑦刻蚀钝化层］的光刻板



> 第四层：［⑧沉积PAD金属+场板］的光刻板



> 光刻板总览